Deep trap engineering in Gd₃GaO₆:Bi³⁺ persistent phosphors through co-doping lanthanide ions

Chengxue Du^a, Dangli Gao^{*ab}, Xiaochun Hou^a, Xiangyu Zhang^c, Qing Pang^b and Sining Yun^d

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^a School of Environmental and Municipal Engineering, Xi'an University of Architecture

and Technology, Xi'an, Shaanxi 710055, China

^b College of Science, Xi'an University of Architecture and Technology, Xi'an 710055,

China. E-mail: gaodangli@163.com, gaodangli@xauat.edu.cn

^cCollege of Science, Chang'an University, Xi'an, Shaanxi 710064, China

^d Functional Materials Laboratory (FML), School of Materials Science &

Engineering, Xi'an University of Architecture and Technology, Xi'an, Shaanxi

710055, China



Fig. S1. The Rietveld refinement of pure GGO:Bi and GGO:Bi,Eu.



Fig. S2. PLE spectra of GGO:Bi,Ln³⁺ (Ln=Sm, Dy, Ce and Pr). (a) GGO:Bi,Sm³⁺; (b) GGO:Bi,Dy³⁺; (c) GGO:Bi,Ce³⁺ and (d) GGO:Bi,Pr³⁺.



Fig. S3. PL spectra of GGO:Bi,Ln³⁺ (Ln=Sm, Dy, Ce and Pr).



Fig. S4. PersL and TL spectra of GGO:Bi,Ln³⁺ (Ln=Sm, Dy, Ce and Pr). (a,b) PersL spectra and TL curves. Before the measurement of PersL and PSL, the samples have been pre-irradiated for 3 min.



Fig. S5. Comparison of PL, PersL and PSL emission spectra in GGO:Bi,Tb³⁺. (a) PL spectrum; (b) PersL spectrum and (c) PSL spectra. Before the measurement of PersL and PSL, the sample has been pre-irradiated for 3 min.